

FORM PTO-1449	US DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	FEB 05 2004 P A T E N T & T R A D E M A R K O F F I C E	Atty. Docket No. <b>86655SHS</b> Customer No. 01333	Serial No. <b>10/722,309</b>
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## LIST OF ART CITED BY APPLICANT

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Filing Date  
**25 November 2003**

Group

## U.S. PATENT DOCUMENTS

Examiner Initials	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
V	US 2003/0173895 A1	09-18-2003	Yoshifumi Kato et al.	313	504	01-30-2003
	5,920,080	07-06-1999	Gary W. Jones	257	40	05-08-1998
	6,198,218	03-06-2001	Koji Kobashi et al.	313	504	12-18-1998
	6,525,335	02-25-2003	Michael R. Krames et al.	257	13	11-06-2000
	6,560,398	05-06-2003	William R. Roach et al.	385	147	10-19-2000
	6,608,449	08-19-2003	Takeshi Fukanaga	313	169.3	05-08-2001

## FOREIGN PATENT DOCUMENTS

Examiner Initials	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES   NO

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

✓	A. Gicquel, K. Hassouni, F. Silva and J. Achard, "CVD diamond films: from growth to applications," <i>Current Applied Physics</i> 1 (2001), pp. 479-496.
	"Diamond Films" Recent Developments," Volume 23, No. 9 of the MRS Bulletin (September 1998), Materials Research Society, Warrendale, Pennsylvania.
✓	L.L. Regel and W.R. Wilcox, "Diamond film deposition by chemical vapor transport," <i>Acta Astronautica</i> 48 (2001), pp. 129-144.
✓	W.L. Wang, K.J. Liao, R.Q. Zhang and C.Y. Kong, "Investigation of organic light emitting devices using boron-doped diamond electrodes," <i>Materials Science and Engineering B85</i> (2001), pp. 169-171.
✓	M.J. Ulczynski, B. Wright and D.K. Reinhard, "Diamond-coated glass substrates," <i>Diamond and Related Materials</i> 7 (1998), pp. 1639-1646.
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✓	C. Jinsheng, W. Xuejun, Z. Zhihao and Y. Fengyuan, "Nucleation and growth of diamond on silicon substrate coated with polymer," <i>Thin Solid Films</i> 346 (1999), pp. 120-124.
✓	Z. Sun, X. Shi, X. Wang, B.K. Tay, H. Yang and Y. Sun, "Morphological features of diamond films depending on substrate temperatures via a low pressure polymer precursor process in a hot filament reactor," <i>Diamond and Related Materials</i> 7 (1998), pp. 939-943.
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✓	L. Dong, B. Ma and G. Dong, "Diamond deposition at low temperature by using CH <sub>4</sub> /H <sub>2</sub> gas mixture," <i>Diamond and Related Materials</i> 11 (2002), pp. 1697-1702.
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	L.L. Regel and W.R. Wilcox, "Deposition of diamond on graphite and carbon felt from graphite heated in hydrogen at low pressure," <i>J. Mat. Sci. Lettr.</i> 19 (2000), pp. 455-457.

EXAMINER

DATE CONSIDERED

9/24/05

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



FORM EKC-1449 		Atty. Docket No. <b>86655SHS</b> Customer No. 01333		Serial No. <b>US 10/722,309</b>	
If AFTER the later date of the first Office Action or 3 months from issue of Certificate or Fee use only with Rule 97(E)		Applicant: <b>Liya Regel, et al</b>			
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <small>(Use several sheets if necessary)</small>		Filing Date <b>25 November 2003</b>		Group <b>1762</b>	
<b>U.S. PATENT DOCUMENTS</b>					
Examiner Initials	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS
	S,863,324	01-26-1999	Koji Kobashi et al.	117	89
	US 2003/0108672 A1	06-12-2003	Yoshiki Takagi	427	249.8
	JP 08 225394 A	09-03-1996	Yamagishi Kenichiro	C30 B	29/04
FILING DATE <i>IF APPROPRIATE</i>					
<b>FOREIGN PATENT DOCUMENTS</b>					
Examiner Initials	DOCUMENT NUMBER	DATE	NAME <small>COUNTRY</small>	CLASS	SUBCLASS
	JP 08 225394A	09-03-1996	Kenichiro et al		
TRANSLATION <i>YES      NO</i>					
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>					
EXAMINER	DATE CONSIDERED				
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